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CLAIMS:

1. An electronic device workpiece comprising:
a substrate having a surface;
a temperature sensing device borne by the substrate; and
an electrical interconnect provided upon the surface of the
substrate, the electrical interconnect being electrically coupled with the
temperature sensing device.

2. The electronic device workpiece according to claim 1 further
comprising a wire connection adapted to electrically connect the
electrical interconnect and the temperature sensing device.

3. The electronic device workpiece according to claim 1
wherein the electrical interconnect contacts the temperature sensing
device.

4. The electronic device workpiece according to claim 1
wherein the workpiece has an edge and the electrical interconnect
extends from the temperature sensing device to the edge of the
electronic device workpiece.

1 5. The electronic device workpiece according to claim 1 further
2 comprising a cavity including plural sloped sidewalls and a bottom wall
3 within the substrate, the temperature sensing device being provided
4 within the cavity.

5
6 6. The electronic device workpiece according to claim 5
7 wherein the sidewalls are sloped at an angle within the approximate
8 range of fifty to sixty degrees with respect to the surface of the
9 substrate.

10
11 7. The electronic device workpiece according to claim 1 further
12 comprising an isolator intermediate the surface of the electronic device
13 workpiece and individual ones of the electrical interconnect and the
14 temperature sensing device.

15
16 8. The electronic device workpiece according to claim 1 further
17 comprising an interface connection in electrical connection with the
18 electrical interconnect, the interface connection being configured to
19 provide electrical coupling of the electrical interconnect and the
20 temperature sensing device with circuitry external of the electronic
21 device workpiece.

22
23 9. The electronic device workpiece according to claim 1
24 wherein the electrical interconnect comprises a conductive trace.

1 10. The electronic device workpiece according to claim 1
2 wherein the temperature sensing device comprises a resistance
3 temperature device.

4
5 11. The electronic device workpiece according to claim 1
6 wherein the substrate includes a via and a conductor within the via
7 configured to electrically couple with the electrical interconnect.

8
9 12. The electronic device workpiece according to claim 1 further
10 comprising plural additional temperature sensing devices borne by the
11 substrate.

12
13 13. The electronic device workpiece according to claim 1
14 wherein the electronic device workpiece comprises a calibration
15 workpiece.

16
17 14. The electronic device workpiece according to claim 1
18 wherein the substrate comprises a semiconductive substrate.

19
20 15. The electronic device workpiece according to claim 1
21 wherein the substrate comprises silicon.

22
23 16. The electronic device workpiece according to claim 1
24 wherein the substrate comprises silicon carbide.

1 17. The electronic device workpiece according to claim 1
2 wherein the substrate comprises gallium nitride.

3
4 18. An electronic device workpiece comprising:
5 a substrate having a surface;
6 a cavity formed in the substrate, the cavity having sidewalls sloped
7 at an angle within an approximate range of fifty to sixty degrees with
8 respect to the surface of the substrate;
9 a temperature sensing device within the cavity of the substrate;
10 and
11 an electrical interconnect coupled with the temperature sensing
12 device.

13
14 19. The electronic device workpiece according to claim 18
15 wherein the electrical interconnect is formed upon the surface of the
16 substrate.

17
18 20. The electronic device workpiece according to claim 18
19 further comprising a wire connection electrically connecting the electrical
20 interconnect and the temperature sensing device.

21
22 21. The electronic device workpiece according to claim 18
23 wherein the electrical interconnect contacts the temperature sensing
24 device.

1 22. The electronic device workpiece according to claim 18
2 wherein the workpiece has an edge and the electrical interconnect
3 extends from the temperature sensing device to the edge of the
4 electronic device workpiece.

5
6 23. The electronic device workpiece according to claim 18
7 wherein the sidewalls are sloped at approximately fifty-four degrees.

8
9 24. The electronic device workpiece according to claim 18
10 wherein the electronic device workpiece comprises a semiconductor
11 wafer.

12
13 25. The electronic device workpiece according to claim 18
14 wherein the electronic device workpiece comprises a calibration
15 workpiece.

16
17 26. The electronic device workpiece according to claim 18
18 wherein the electrical interconnect comprises a conductive trace.

19
20 27. The electronic device workpiece according to claim 18
21 wherein the temperature sensing device comprises a resistance
22 temperature device.

1 28. A semiconductor workpiece comprising:
2 a semiconductive substrate having a surface;
3 a temperature sensing device borne by the substrate; and
4 an electrical interconnect provided upon the surface of the
5 substrate, the electrical interconnect being electrically coupled with the
6 temperature sensing device.

7
8 29. The semiconductor workpiece according to claim 28 further
9 comprising a cavity including plural sloped sidewalls and a bottom wall
10 within the substrate, the temperature sensing device being provided
11 within the cavity.

12
13 30. The semiconductor workpiece according to claim 28 wherein
14 the electrical interconnect comprises a conductive trace.
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1 31. A semiconductor workpiece comprising:
2 a substrate having a surface and an edge;
3 a cavity formed in the substrate, the cavity having sidewalls sloped
4 at an approximate fifty-four degree angle with respect to the surface of
5 the substrate;
6 a resistance temperature device within the cavity of the substrate;
7 a plurality of conductive traces coupled with the resistance
8 temperature device, the conductive traces being formed upon the surface
9 of the substrate to contact the resistance temperature device, the
10 conductive traces being configured to electrically couple the resistance
11 temperature device with the edge of the substrate;
12 an isolator intermediate the surface of the electronic device
13 workpiece and the conductive traces and the resistance temperature
14 device; and
15 an interface connection in electrical connection with the conductive
16 traces, the interface connection being configured to provide electrical
17 coupling of the resistance temperature device with circuitry external of
18 the semiconductor workpiece.
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1 32. A method of sensing temperature of an electronic device
2 workpiece comprising:

3 providing an electronic device workpiece;

4 supporting a temperature sensing device using the electronic device
5 workpiece;

6 providing an electrical interconnect upon a surface of the
7 electronic device workpiece;

8 electrically coupling the electrical interconnect with the temperature
9 sensing device; and

10 sensing temperature of the electronic device workpiece using the
11 temperature sensing device.

12
13 33. The method according to claim 32 further comprising wire
14 bonding the electrical interconnect and the temperature sensing device.

15
16 34. The method according to claim 32 further comprising:

17 forming a cavity in the electronic device workpiece; and

18 providing the temperature sensing device within the cavity.

19
20 35. The method according to claim 34 wherein the forming the
21 cavity comprises anisotropically etching the electronic device workpiece.

22
23 36. The method according to claim 34 wherein the forming the
24 cavity comprises isotropically etching the electronic device workpiece.

1 37. The method according to claim 32 further comprising
2 forming the temperature sensing device.

3
4 38. The method according to claim 37 wherein the forming the
5 temperature sensing device comprises forming a resistance temperature
6 device.

7
8 39. The method according to claim 32 further comprising
9 electrically coupling the electrical interconnect with external circuitry.

10
11 40. The method according to claim 32 further comprising
12 electrically coupling the temperature sensing device with an edge of the
13 electronic device workpiece using the electrical interconnect.

14
15 41. The method according to claim 32 wherein the providing the
16 electrical interconnect comprises forming a conductive trace.

17
18 42. The method according to claim 32 further comprising
19 contacting the electrical interconnect with the temperature sensing device.

20
21 43. The method according to claim 32 wherein the method
22 comprises a method of sensing temperature of semiconductor wafers.

1 44. A method of semiconductor processing, comprising:
2 providing a semiconductor substrate;
3 anisotropically etching a cavity in the semiconductor substrate; and
4 providing a temperature sensing device within the cavity of the
5 semiconductor substrate.

6
7 45. The method according to claim 44 further comprising:
8 providing an electrical interconnect upon a surface of the
9 semiconductor substrate; and
10 electrically coupling the electrical interconnect with the temperature
11 sensing device.

12
13 46. The method according to claim 45 wherein the providing the
14 electrical interconnect comprises forming a conductive trace.

15
16 47. The method according to claim 45 wherein the electrically
17 coupling comprises wire bonding the electrical interconnect and the
18 temperature sensing device.

19
20 48. The method according to claim 45 wherein the electrically
21 coupling includes contacting the electrical interconnect and the
22 temperature sensing device.

1 49. The method according to claim 45 further comprising
2 electrically coupling the electrical interconnect with circuitry external to
3 the semiconductor substrate.

4
5 50. The method according to claim 45 further comprising
6 electrically coupling the temperature sensing device with an edge of the
7 semiconductor substrate using the electrical interconnect.

8
9 51. The method according to claim 44 wherein the providing
10 comprises forming the temperature sensing device within the cavity.

11
12 52. The method according to claim 44 wherein the providing
13 comprises positioning the temperature sensing device within the cavity.

14
15 53. A method of sensing temperature of an electronic device
16 workpiece comprising:

17 providing an electronic device workpiece;

18 forming a temperature sensing device upon the electronic device
19 workpiece, the forming including providing the temperature sensing
20 device in a temperature sensing relation with the electronic device
21 workpiece; and

22 sensing the temperature of the electronic device workpiece using
23 the temperature sensing device.

24

1 54. The method according to claim 53 further comprising:
2 providing an electrical interconnect upon the electronic device
3 workpiece; and
4 electrically coupling the electrical interconnect with the temperature
5 sensing device.

6
7 55. The method according to claim 54 wherein the providing the
8 electrical interconnect comprises forming a conductive trace.

9
10 56. The method according to claim 54 wherein the electrically
11 coupling comprises wire bonding the electrical interconnect and the
12 temperature sensing device.

13
14 57. The method according to claim 54 wherein the electrically
15 coupling includes contacting the electrical interconnect and the
16 temperature sensing device.

17
18 58. The method according to claim 53 further comprising:
19 forming a cavity in the electronic device workpiece; and
20 providing the temperature sensing device within the cavity.

21
22 59. The method according to claim 58 wherein the forming the
23 cavity comprises anisotropically etching the electronic device workpiece.
24

1 60. The method according to claim 53 wherein the forming
2 comprises forming a resistance temperature device.

3
4 61. The method according to claim 53 further comprising
5 forming plural temperature sensing devices upon the electronic device
6 workpiece.

7
8 62. A method of sensing temperature of an electronic device
9 workpiece comprising:

10 providing an electronic device workpiece;

11 supporting a temperature sensing device using the electronic device
12 workpiece;

13 providing the temperature sensing device in a temperature sensing
14 relation with the electronic device workpiece;

15 providing an electrical interconnect upon a surface of the
16 electronic device workpiece; and

17 electrically coupling the electrical interconnect with the temperature
18 sensing device.

19
20 63. The method according to claim 62 wherein the coupling
21 comprises wire bonding the electrical interconnect and the temperature
22 sensing device.

1 64. The method according to claim 62 wherein the coupling
2 comprises contacting the electrical interconnect with the temperature
3 sensing device.

4
5 65. The method according to claim 62 further comprising:
6 forming a cavity in the electronic device workpiece; and
7 providing the temperature sensing device within the cavity.

8
9 66. The method according to claim 65 wherein the forming the
10 cavity comprises anisotropically etching the electronic device workpiece.

11
12 67. The method according to claim 62 further comprising
13 forming a temperature sensing device upon the electronic device
14 workpiece.

15
16 68. The method according to claim 62 further comprising
17 electrically coupling the electrical interconnect with circuitry external to
18 the electronic device workpiece.

19
20 69. The method according to claim 62 further comprising
21 electrically coupling the temperature sensing device with an edge of the
22 electronic device workpiece using the electrical interconnect.

1 70. The method according to claim 62 wherein the providing the
2 electrical interconnect comprises forming a conductive trace.
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